Abstract of the Disclosure

Disclosed is a high-performance, RF-capable MIM capacitor structure and process for the manufacture thereof, which are compatible with discrete or integrated processes. The invention is compatible with standard semiconductor processing techniques and provides increased capacitance per unit area for a wide variety of capacitor requirements. The invention exploits vertical dimensions, reduces the chip area required for capacitors, and facilitates the use of advanced materials, such as high-k dielectric materials.